

Product Specification

XBLW AO3400

N-Channel Enhancement Mode MOSFET











Description

The AO3400 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

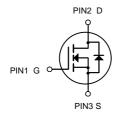
- > VDS = 30V,ID = 5.8A
- ightharpoonup RDS(ON) < 28m Ω @ VGS=10V
- \triangleright RDS(ON) < 34m Ω @ VGS=4.5V

Application

- > High power and current handing capability
- Lead free product is acquired
- Surface mount package
- > PWM applications
- Load switch
- Power management



SOT-23-3L



N-Channel MOSFET

Package Marking and Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
XBLW AO3400	SOT-23-3L	X0VX	Tape	3000Pcs/Reel

Absolute Maximum Ratings (TA=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	5.8	Α
Ірм	Drain Current-Pulsed (Note 1)	30	А
P _D	Maximum Power Dissipation	1.4	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Røja	Thermal Resistance, Junction-to-Ambient (Note 2)	89	°C/W



Electrical Characteristics (TA=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	-		-			•
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	Ipss	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	0.7	0.9	1.4	V
		V _{GS} =2.5V, I _D =4A	-	41	55	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =4.5V, I _D =5A	-	23	34	mΩ
		V _{GS} =10V, I _D =5.8A	-	21	28	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =5A	10	-	-	S
Input Capacitance	Clss	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	825	-	PF
Output Capacitance	Coss		-	100	-	PF
Reverse Transfer Capacitance	C _{rss}		-	78	-	PF
Turn-on Delay Time	td(on)	-		3.3	-	nS
Turn-on Rise Time	tr	V_{DD} =15V, R_L =2.7 Ω V_{GS} =10V, R_{GEN} =3 Ω	-	4.8	-	nS
Turn-Off Delay Time	td(off)		-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Qg	V _{DS} =15V,I _D =5.8A,	-	10	-	nC
Gate-Source Charge	Q _{gs}		1.6	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	3.1	-	nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =5.8A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	5.8	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

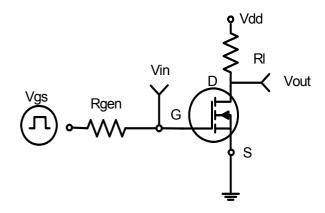


Figure 1:Switching Test Circuit

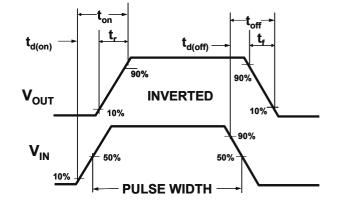


Figure 2:Switching Waveforms

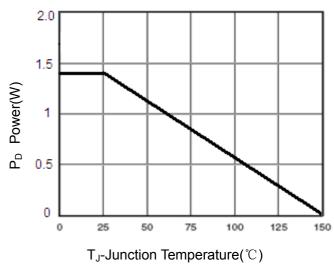


Figure 3 Power Dissipation

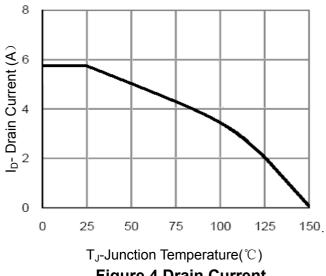


Figure 4 Drain Current

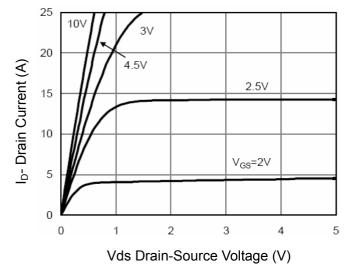


Figure 5 Output Characteristics

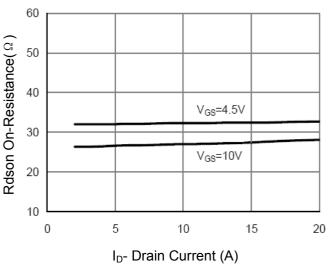


Figure 6 Drain-Source On-Resistance

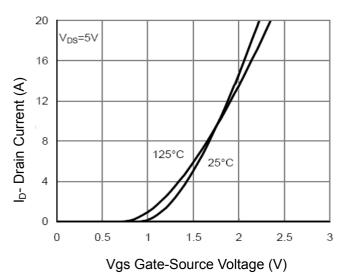


Figure 7 Transfer Characteristics

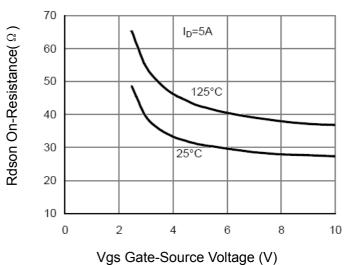


Figure 9 Rdson vs Vgs

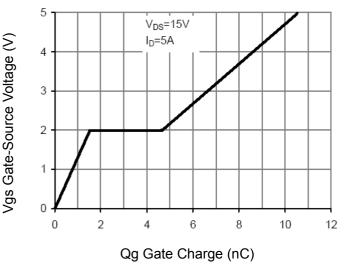


Figure 11 Gate Charge

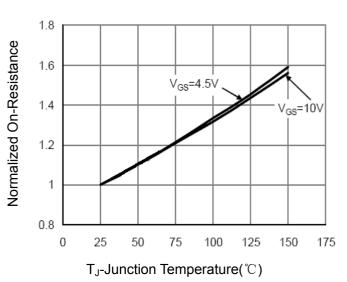


Figure 8 Drain-Source On-Resistance

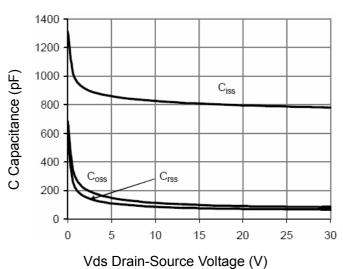


Figure 10 Capacitance vs Vds

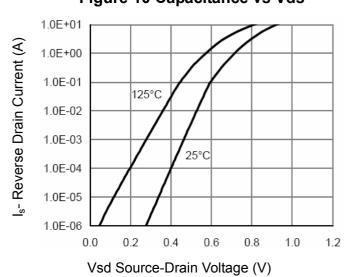


Figure 12 Source- Drain Diode Forward

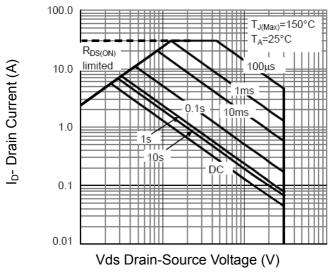


Figure 13 Safe Operation Area

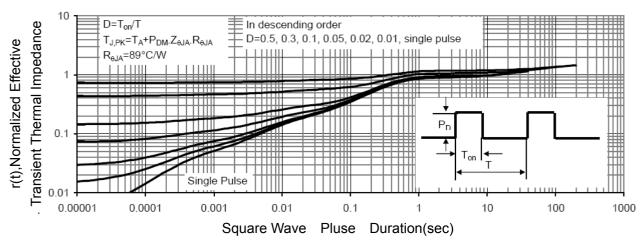
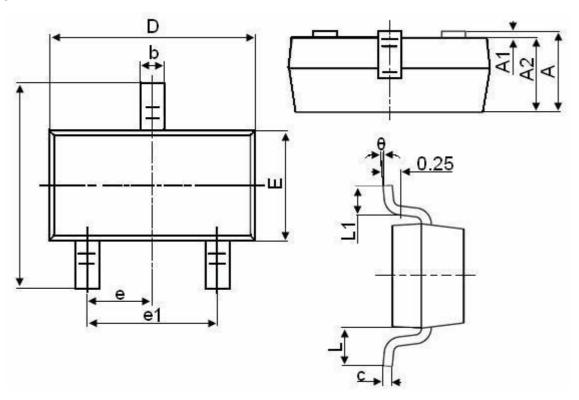


Figure 14 Normalized Maximum Transient Thermal Impedance



Package Information

SOT23-3L



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.600		
θ	0°	8°		



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